



2DA1213O

PNP SURFACE MOUNT TRANSISTOR

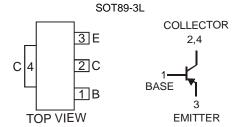
Features

- **Epitaxial Planar Die Construction**
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
 - "Green" Device (Note 2)

Mechanical Data

- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3 Ordering Information: See Page 3
- Weight: 0.072 grams (approximate)





Schematic and Pin Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-50	V
Collector-Emitter Voltage	V _{CEO}	-50	V
Emitter-Base Voltage	V _{EBO}	-5	V
Continuous Collector Current	Ic	-2	A
Base Current	I _B	-0.4	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T _A = 25°C	P_{D}	1	W
Thermal Resistance, Junction to Ambient Air (Note 3) @ T _A = 25°C	$R_{ heta JA}$	125	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Min	Тур	Max	Unit	Conditions
OFF CHARACTERISTICS	OFF CHARACTERISTICS (Note 4)						
Collector-Base Breakdow	n Voltage	V _{(BR)CBO}	-50			V	$I_C = -100\mu A, I_E = 0$
Collector-Emitter Breakdo	Collector-Emitter Breakdown Voltage		-50			V	$I_C = -10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage		V _{(BR)EBO}	-5	_	_	V	$I_E = -100 \mu A, I_C = 0$
Collector Cut-Off Current		I _{CBO}	_		-0.1	μΑ	$V_{CB} = -50V, I_{E} = 0$
Emitter Cut-Off Current		I _{EBO}	_	_	-0.1	μΑ	$V_{EB} = -5V, I_C = 0$
ON CHARACTERISTICS (Note 4)							
Collector-Emitter Saturation Voltage		V _{CE(SAT)}	_	_	-0.5	V	$I_C = -1A$, $I_B = -50mA$
Base-Emitter Saturation Voltage		V _{BE(SAT)}			-1.2	V	$I_C = -1A$, $I_B = -50mA$
DC Current Gain	2DA1213O	h _{FE}	70		140	_	$V_{CE} = -2V, I_{C} = -0.5A$
	2DA1213Y		120		240	_	$V_{CE} = -2V, I_{C} = -0.5A$
	2DA1213O, 2DA1213Y		20	_	_	_	$V_{CE} = -2V, I_{C} = -2A$
SMALL SIGNAL CHARACTERISTICS							
Transition Frequency		f⊤		160	_	MHz	$V_{CE} = -2V$, $I_{C} = -100$ mA, $f = 100$ MHz
Output Capacitance		C _{obo}	_	17		pF	$V_{CB} = -10V$, $I_E = 0$, $f = 1MHz$
SWITCHING CHARACTERISTICS							
Turn-On Time		ton	_	25	_	ns	V 2V I 1A
Storage Time		ts	_	130	_	ns	$V_{CE} = -2V, I_{C} = -1A,$ $I_{B1} = -I_{B2} = -50mA$
Fall Time		t _f		12		ns	1B1 = -1B2 = -30111A

Notes: No purposefully added lead.

- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤2%.



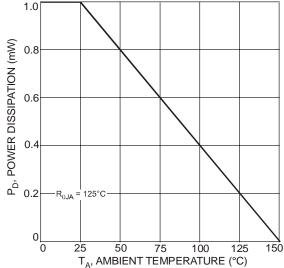
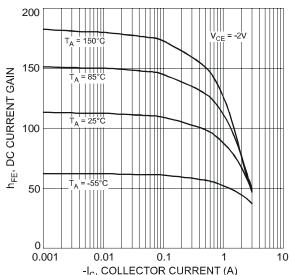


Fig. 1 Power Dissipation vs. Ambient Temperature



-I_C, COLLECTOR CURRENT (A) Fig. 3 Typical DC Current Gain vs. Collector Current (2DA1213O)

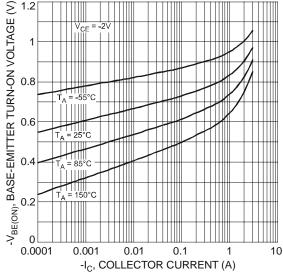


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

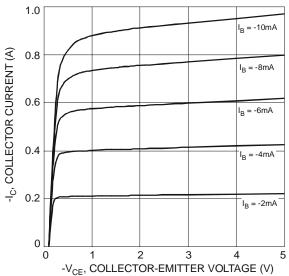


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

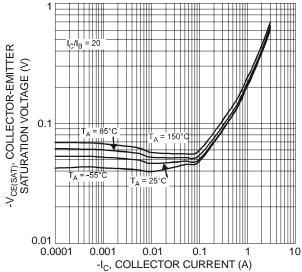


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

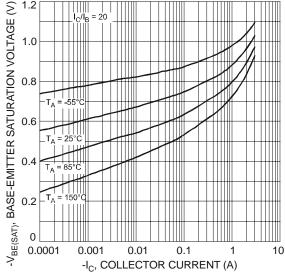
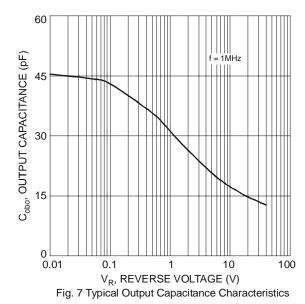


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current





f_T, CURRENT GAIN-BANDWIDTH PRODUCT (MHz) $V_{CE} = -6V$ f = 100MHz0 10 30 70 40 50 60 -I_C, COLLECTOR CURRENT (mA)

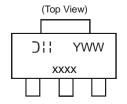
Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

Ordering Information (Note 5)

Device	Packaging	Shipping
2DA1213O-13	SOT89-3L	2500/Tape & Reel
2DA1213Y-13	SOT89-3L	2500/Tape & Reel

5. For packaging details, please see below or go to our website at http://www.diodes.com/ap02007.pdf.

Marking Information



xxxx = Product Type Marking Code:

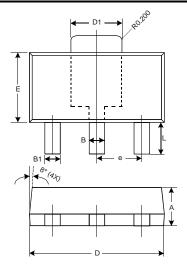
P25X = 2DA1213O

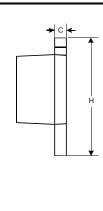
P25Y = 2DA1213Y

YWW = Date Code Marking Y = Last digit of year ex: 7 = 2007

WW = Week code 01 - 52

Package Outline Dimensions

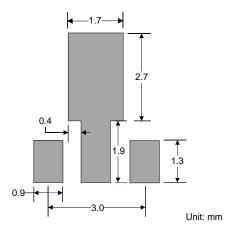




SOT89-3L					
Dim	Min	Max	Тур		
Α	1.40	1.60	1.50		
В	0.45	0.55	0.50		
B1	0.37	0.47	0.42		
С	0.35	0.43	0.38		
D	4.40	4.60	4.50		
D1	1.50	1.70	1.60		
Е	2.40	2.60	2.50		
е		_	1.50		
Н	3.95	4.25	4.10		
L	0.90	1.20	1.05		
All Dimensions in mm					



Suggested Pad Layout



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